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Jan 7, 1997

DERWENT-ACC-NO: 1997-117784

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TITLE: Group III nitride laser structure - formed on a conductive silicon carbide substrate**Basic Abstract Text:**

A separate-confinement heterostructure laser comprises: an InGaN active layer; upper and lower waveguide layers on the active layer formed from the group consisting of AlGaN, InGaN, and AlInGaN; upper and lower cladding layers on the respective upper and lower waveguide layers and formed of AlGaN.

Basic Abstract Text (1):

A separate-confinement heterostructure laser comprises: an InGaN active layer; upper and lower waveguide layers on the active layer formed from the group consisting of AlGaN, InGaN, and AlInGaN; upper and lower cladding layers on the respective upper and lower waveguide layers and formed of AlGaN.

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